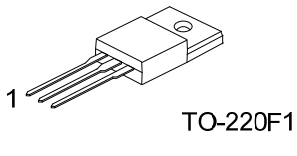
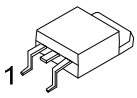
4N65-S

Power MOSFET

4.0A, 650V N-CHANNEL POWER MOSFET



TO-220F1



TO-252

PDFN5×6

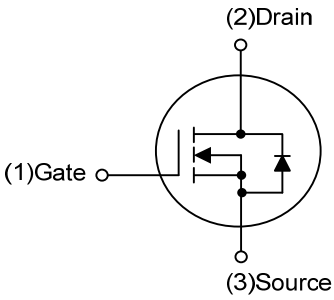
■ DESCRIPTION

The UTC **4N65-S** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

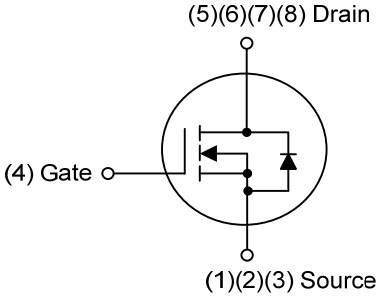
■ FEATURES

* $R_{DS(ON)} \leq 2.9\ \Omega$ @ V_{GS}=10V, I_D=2.0A
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL



TO-220F1/TO-252

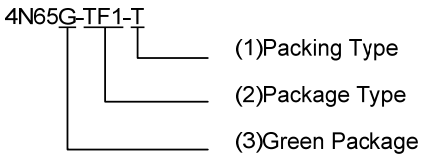


PDFN5×6

■ ORDERING INFORMATION

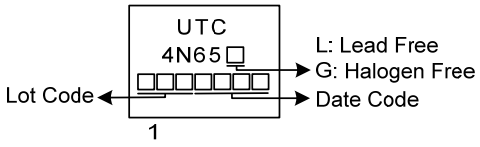
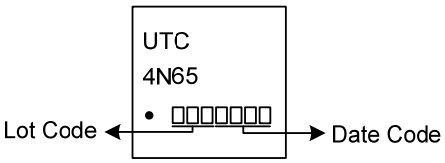
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
4N65L-TF1-T	4N65G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
4N65L-TN3-T	4N65G-TN3-T	TO-252	G	D	S	-	-	-	-	-	Tape Reel
4N65L-P5060-R	4N65G-P5060-R	PDFN5×6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TF1: TO-220F1, TN3: TO-252, P5060: PDFN5×6
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

TO-220F1 / TO-252	PDFN5×6
	

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	150	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F1	P_D	36	W
	TO-252		50	W
	PDFN5×6		30	W
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 18.75mH, I_{AS} = 4A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD}≤4A, di/dt ≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	°C/W
	TO-252		110	°C/W
	PDFN5×6		75 (Note)	°C/W
Junction to Case	TO-220F1	θ_{JC}	3.47	°C/W
	TO-252		2.5	°C/W
	PDFN5×6		4.17 (Note)	°C/W

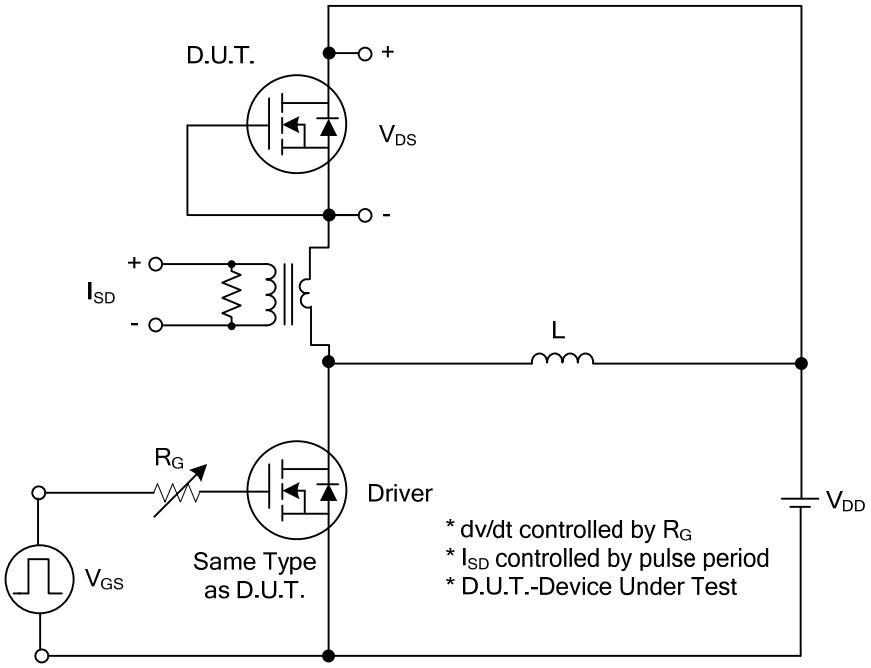
Note: Note: The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

■ ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

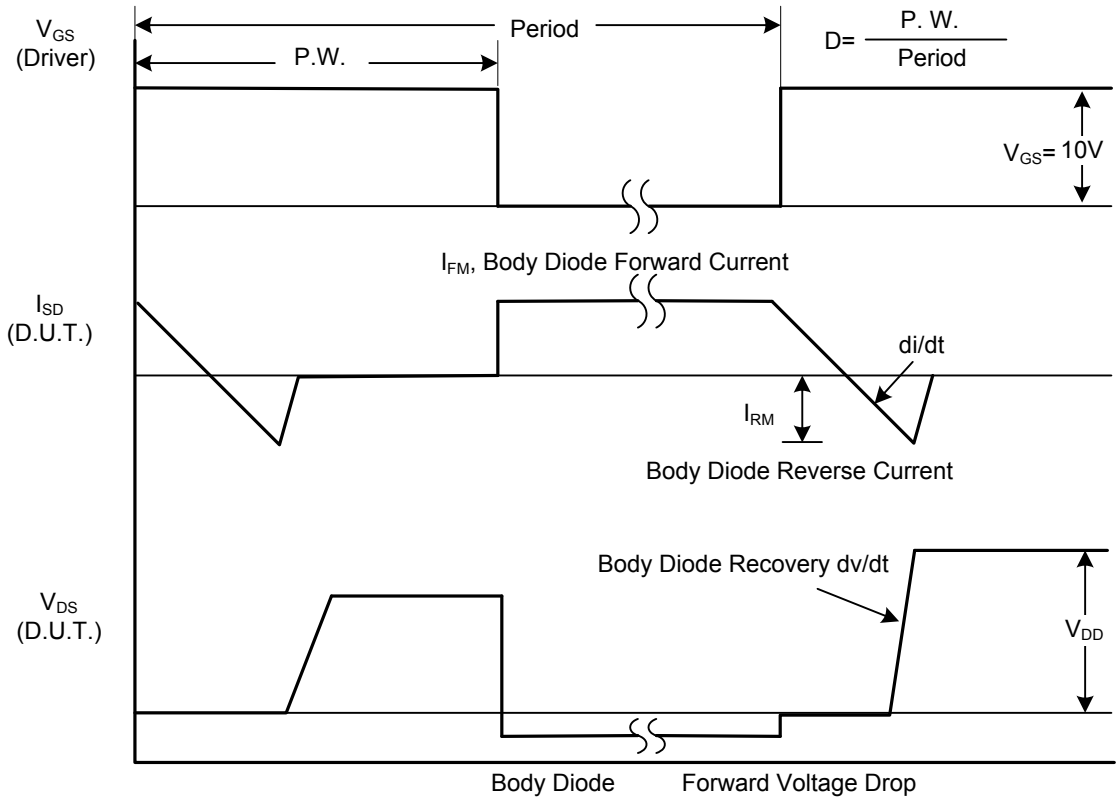
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 650 V, V_{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30 V, V_{DS} = 0 V			100	nA
	Reverse		V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 2.0A			2.9	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} = 25 V, V_{GS} = 0V, f = 1MHz		420	550	pF
Output Capacitance		C_{OSS}			40	60	pF
Reverse Transfer Capacitance		C_{RSS}			4	8	pF
SWITCHING CHARACTERISTICS10							
Total Gate Charge		Q_G	V_{DS}= 50 V,I_D= 1.3 A, V_{GS}= 10V (Note 1, 2)		15	20	nC
Gate-Source Charge		Q_{GS}			5		nC
Gate-Drain Charge		Q_{GD}			2		nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DS} = 30 V, I_D = 0.5 A, R_G = 25Ω (Note 1, 2)		60		ns
Turn-On Rise Time		t_R			25		ns
Turn-Off Delay Time		$t_{D(OFF)}$			125		ns
Turn-Off Fall Time		t_F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				4	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				16	A
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 4A			1.4	V

Note: 1. Pulse Test: Pulse width≤300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

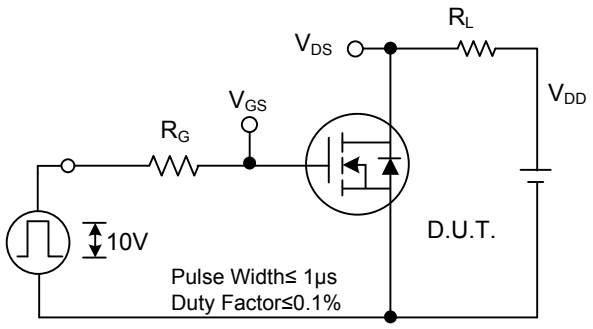


Peak Diode Recovery dv/dt Test Circuit

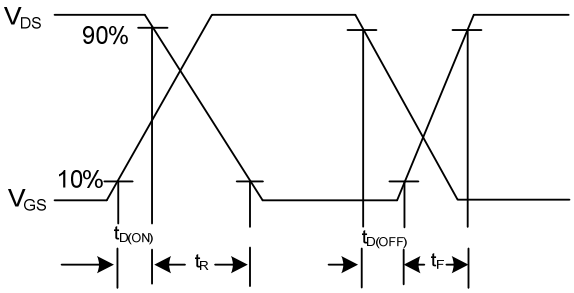


Peak Diode Recovery dv/dt Waveforms

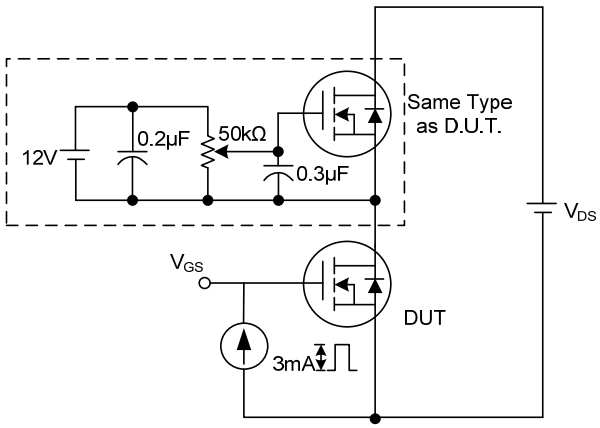
■ TEST CIRCUITS AND WAVEFORMS



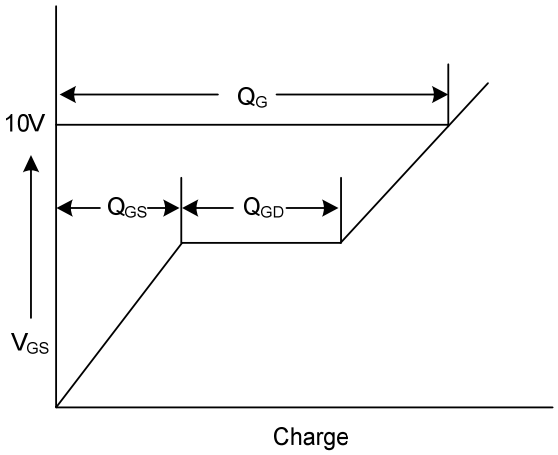
Switching Test Circuit



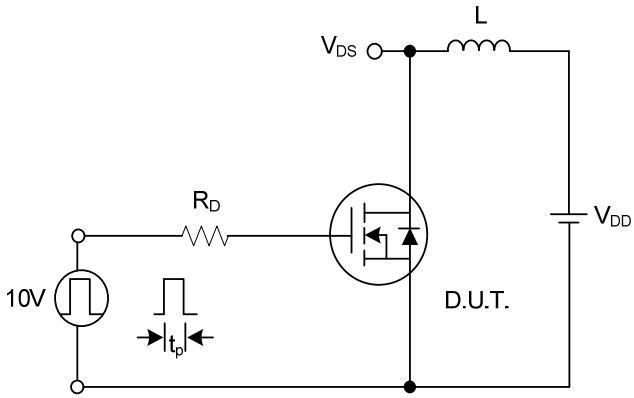
Switching Waveforms



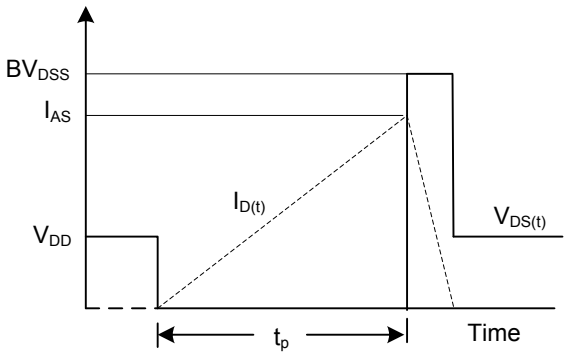
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms